

Abstract Submitted  
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**Particle Jumps in SiO<sub>2</sub>: A Computer Simulation**<sup>1</sup> ROBIN BJORKQUIST, Reed College, KATHARINA VOLLMAYR-LEE, Bucknell University, JUERGEN HORBACH, DLR, Koeln, Germany — We use molecular dynamics simulations to investigate the aging dynamics of SiO<sub>2</sub> modeled by the BKS potential. The system is well equilibrated at temperature  $T_{\text{high}}$  and then quenched to  $T_{\text{low}}$ . We characterize the dynamics by means of jumps in single-particle trajectories and measure the number of jump events, the number of jumping particles, and jump size. All measured quantities increase with increasing  $T_{\text{low}}$  and decrease with increasing waiting time. For the largest investigated temperatures  $T_{\text{low}}$  and for long enough waiting times the system reaches equilibrium and all measured quantities become independent of  $T_{\text{high}}$  and waiting time.

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